

L15 ANSWER 9 OF 12 HCPLUS COPYRIGHT 2003 ACS on STN  
 AN 1999:796011 HCPLUS  
 DN 132:43780  
 TI Formation of dielectric layers  
 IN Narwankar, Pravin K.; Sahin, Turgut; Urdahl, Randall S.; Velaga, Ankineedu; Liu, Patricia  
 PA Applied Materials, Inc., USA  
 SO PCT Int. Appl., 41 pp.  
 CODEN: PIXXD2  
 DT Patent  
 LA English  
 IC ICM C23C016-56  
 ICS C23C016-40; H01L021-3105  
 CC 76-10 (Electric Phenomena)  
 Section cross-reference(s): 75

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 9964645	A1	19991216	WO 1999-US13300	19990611
	W: JP, KR RW: AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE				
	US 2002009861	A1	20020124	US 1998-96858	19980612
	EP 1093532	A1	20010425	EP 1999-930223	19990611
	R: BE, DE, GB, NL, IE				
	JP 2002517914	T2	20020618	JP 2000-553633	19990611
PRAI	US 1998-96858	A	19980612		
	WO 1999-US13300	W	19990611		
AB	An active at. species is generated in a 1st chamber. A dielec. layer formed on a substrate is then exposed to the active at. species in a 2nd chamber sep. from the 1st chamber.				
IT	6074-84-6, Pentaethoxytantalum 172901-22-3 RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses) (in formation of dielec. layers)				
RN	6074-84-6 HCPLUS				
CN	Ethanol, tantalum(5+) salt (9CI) (CA INDEX NAME)				

 $\text{H}_3\text{C}-\text{CH}_2-\text{OH}$ 

1/5 Ta(V)

RN 172901-22-3 HCPLUS  
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23) - (9CI) (CA INDEX NAME)

